NSN 5961-00-845-1245

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-845-1245 **Inclosure Material:** Metal **Overall Length:** Between 0.330 inches and 0.505 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.544 inches and 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 2.0 forward voltage, peak and 3.0 gate trigger voltage, dc **Current Rating Per Characteristic:** 16.00 amperes forward current, total rms megahertz **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Internal junction configuration arrangement pnpn **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator: Terminal Type And Quantity:** 3 tab, solder lug **Specification Data:** 81349-mil-s-19500/108 government specification Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

No

Demilitarization: